

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device includes a semiconductor substrate on which a semiconductor thin film including an active layer is laminated, a pair of electrodes respectively provided on
5 opposite faces of the substrate, a light emitting surface defined on a side face of the substrate to which the active layer and an edge of at least one of the electrodes are exposed, and a protective film covering the light emitting surface. The protective film has a smaller thickness on the edge of the electrode than on the active
10 layer. This arrangement makes it possible to suppress diffusion of an electrode material in the protective film and sufficiently protect the light emitting surface.